

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (canceled)

Claim 2 (currently amended): A plasma reactor for processing a workpiece, said plasma reactor comprising:

an enclosure;

a workpiece support within the enclosure facing an overlying portion of the enclosure, said workpiece support and the overlying portion of said enclosure defining a process region therebetween extending generally across the diameter of said wafer support;

said enclosure having an opening at least first and second openings therethrough near generally opposite sides of said workpiece support;

at least one hollow conduit outside of said process region and connected to said opening first and second openings, providing a first torroidal path extending through said conduit and across said process region;

a first coil antenna adapted to accept RF power, and inductively coupled to the interior of said hollow conduit and capable of maintaining a plasma in said torroidal path; and

wherein said hollow conduit comprises a plenum extending around an axis of symmetry of said chamber and wherein said opening is first and second openings are comprised within a continuous opening in said enclosure extending around the axis of symmetry of said chamber.

Claim 3 (original): The plasma reactor of Claim 2 wherein

said plenum and said continuous opening extend 360 degrees around the axis of symmetry of said enclosure.

Claim 4 (previously presented): A plasma reactor for processing a workpiece, said plasma reactor comprising:
an enclosure;

a workpiece support within the enclosure facing an overlying portion of the enclosure, said workpiece support and the overlying portion of said enclosure defining a process region therebetween extending generally across the diameter of said wafer support;

said enclosure having at least first and second openings therethrough near generally opposite sides of said workpiece support;

at least one hollow conduit outside of said process region and connected to said first and second openings, providing a first torroidal path extending through said conduit and across said process region;

a first coil antenna adapted to accept RF power, and inductively coupled to the interior of said hollow conduit and capable of maintaining a plasma in said torroidal path; and

wherein said conduit is formed of a metal material, said conduit having an insulating gap within a wall of the conduit extending transversely to said torroidal path and separating said conduit into two portions so as to prevent formation of a closed electrical path along the length of said conduit.

Claim 5 (previously presented): The plasma reactor of Claim 2 wherein said coil antenna is wound around an axis generally parallel with an axis of said closed torroidal path.

Claim 6 (original): The plasma reactor of Claim 5 wherein said coil antenna comprises a first winding extending on one side of and along said conduit.

Claim 7 (previously presented): A plasma reactor for processing a workpiece, said plasma reactor comprising:
an enclosure;

a workpiece support within the enclosure facing an overlying portion of the enclosure, said workpiece support and the overlying portion of said enclosure defining a process region therebetween extending generally across the diameter of said wafer support;

said enclosure having at least first and second openings therethrough near generally opposite sides of said workpiece support;

at least one hollow conduit outside of said process region and connected to said first and second openings, providing a first torroidal path extending through said conduit and across said process region;

a first coil antenna adapted to accept RF power, and inductively coupled to the interior of said hollow conduit and capable of maintaining a plasma in said torroidal path;

wherein said coil antenna is wound around an axis generally parallel with the axis of said closed torroidal path;

wherein said coil antenna comprises a first winding extending on one side of and along said conduit; and

wherein said coil antenna comprises a second winding extending on an opposite side of and along said conduit.

Claim 8 (previously presented): The plasma reactor of Claim 7 wherein said coil antenna comprises a winding disposed between said conduit and said enclosure.

Claim 9 (original): The plasma reactor of Claim 8 wherein said winding has an outer diameter less than an inner diameter of said conduit.

Claim 10 (previously presented): The plasma reactor of Claim 7 further comprising at least one magnetic core extending between said enclosure and said conduit in a direction generally parallel to the axis of said closed toroidal path, said first winding extending around said magnetic core.

Claim 11 (original): The plasma reactor of Claim 7 further comprising at least one magnetic core extending between said enclosure and said conduit in a direction generally parallel to the axis of said closed toroidal path, said first and second windings extending around said magnetic core.

Claim 12 (original): The plasma reactor of Claim 8 further comprising at least one magnetic core extending between said enclosure and said conduit in a direction generally parallel to the axis of said closed toroidal path, said winding extending around said magnetic core.

Claim 13 (currently amended): The plasma reactor of Claim [[2]] 4 further comprising a closed magnetic core surrounding said conduit so as to have one portion of the magnetic core extending through a region between said enclosure and said conduit, said coil antenna being wound around said closed magnetic core.

Claim 14 (original): The plasma reactor of Claim 13 wherein said closed magnetic core has a second portion outside the region

between said enclosure and said conduit, said coil antenna being wound around a section of said second portion.

Claim 15 (previously presented): A plasma reactor for processing a workpiece, said plasma reactor comprising:

an enclosure;

a workpiece support within the enclosure facing an overlying portion of the enclosure, said workpiece support and the overlying portion of said enclosure defining a process region therebetween extending generally across the diameter of said wafer support;

said enclosure having at least first and second openings therethrough near generally opposite sides of said workpiece support;

at least one hollow conduit outside of said process region and connected to said first and second openings, providing a first toroidal path extending through said conduit and across said process region;

a first coil antenna adapted to accept RF power, and inductively coupled to the interior of said hollow conduit and capable of maintaining a plasma in said toroidal path;

an array of pairs openings through said vacuum enclosure, each pair of openings near generally opposite sides of said workpiece support; and

an array of generally mutually parallel hollow conduits outside of said vacuum chamber that includes said one hollow conduit, and connected to respective ones of said pairs of openings, whereby to provide respective closed toroidal paths for plasma, each of said respective closed toroidal paths extending outside of said vacuum chamber through a respective one of said array of conduits and extending inside said vacuum chamber between a respective pair of said openings across said

wafer surface.

Claim 16 (original): The reactor of Claim 15 further comprising an array of antenna coils, each one of said antenna coils being inductively coupled to the interior of a respective one of said array of hollow conduits and capable of maintaining a plasma current in a respective one of said closed toroidal paths.

Claim 17 (original): The reactor of Claim 16 further comprising plural separately adjustable RF power sources coupled to respective ones of said array of coil antennas, whereby the plasma ion density distribution across the surface of said workpiece is adjustable through individual adjustment of said plural RF power sources.

Claim 18 (original): The reactor of Claim 17 further comprising plural discrete magnetic cores confined generally to respective regions between respective ones of said array of conduits and said enclosure, each of said array of coil antennas being wound around a respective one of said plural discrete magnetic cores.

Claim 19 (original): The reactor of Claim 15 further comprising a common magnetic core extending between said array of hollow conduits and said enclosure, said coil antenna being wound around said common magnetic core.

Claim 20 (currently amended): The reactor of Claim [[2]] 4 wherein said conduit has a width along an axis parallel with a plane of said wafer support which is at least as great as the diameter of said wafer support.

Claim 21 (original): The reactor of Claim 20 wherein said conduit has a height along an axis perpendicular to the plane of said wafer support which is less than said width.

Claim 22 (original): The reactor of Claim 21 wherein said conduit has a rectangular cross-section whereby to produce a relatively thin wide belt of plasma in said closed toroidal path.

Claim 23 (previously presented): A plasma reactor for processing a workpiece, said plasma reactor comprising:

an enclosure;

a workpiece support within the enclosure facing an overlying portion of the enclosure, said workpiece support and the overlying portion of said enclosure defining a process region therebetween extending generally across the diameter of said wafer support;

said enclosure having at least first and second openings therethrough near generally opposite sides of said workpiece support;

at least one hollow conduit outside of said process region and connected to said first and second openings, providing a first toroidal path extending through said conduit and across said process region;

a first coil antenna adapted to accept RF power, and inductively coupled to the interior of said hollow conduit and capable of maintaining a plasma in said toroidal path; and

wherein the height of said closed toroidal path along an axis generally perpendicular to a plane of said wafer support in a process region overlying said workpiece support is less than elsewhere in said closed toroidal path, whereby to enhance the

plasma ion density in said process region relative to the plasma ion density elsewhere in said closed torroidal path.

Claim 24 (previously presented): The plasma reactor of Claim 23 further comprising a conductive body between said workpiece support and said vacuum enclosure and constricting said torroidal path in a processing region overlying said wafer support.

Claim 25 (canceled)

Claim 26 (canceled)

Claim 27 (previously presented): The plasma reactor of Claim 23 further comprising an RF bias power supply coupled to said workpiece support capable of maintaining a plasma sheath over a workpiece on said workpiece support of a thickness which constricts said closed torroidal path so as to enhance plasma ion density in a process region overlying said workpiece support.

Claim 28 (previously presented): The plasma reactor of Claim 23 further comprising an RF bias power supply coupled to said workpiece support.

Claim 29 (canceled)

Claim 30 (original): The plasma reactor of Claim 21 further comprising:

a first magnetic core extending between said conduit and said enclosure across at least a portion of a first half of said width, said coil antenna comprising a first winding surrounding said first magnetic core;

a second magnetic core extending between said conduit and said enclosure across at least a portion of a remaining half of said width, said coil antenna further comprising a second winding wound surrounding said second magnetic core.

Claim 31 (previously presented): The plasma reactor of Claim 30 wherein said first and second magnetic cores are longitudinally movable toward and away from a center locus overlying a center of said wafer support, whereby to enable adjustment of plasma ion density near the center of said workpiece support relative to plasma ion density near a periphery of said wafer support.

Claim 32 (previously presented): The plasma reactor of Claim 30 wherein said first and second windings are closely wound around said first and second magnetic cores respectively.

Claim 33 (original): The plasma reactor of Claim 31 wherein said first and second windings comprise a continuous winding having first and second portions around said first and second magnetic cores respectively.

Claim 34 (previously presented): The plasma reactor of Claim 23 wherein said enclosure comprises a longitude side wall and an overlying lateral ceiling, and wherein said first and second openings extend through said ceiling.

Claim 35 (canceled)

Claim 36 (previously presented): The reactor of Claim 23 wherein said conduit is elongate and tubular of a cross-sectional shape that is one of curved or rectangular, said first and second

openings mating with respective ends of said conduit.

Claim 37 (original): The reactor of Claim 30 wherein said conduit has a smaller cross-sectional area at an intermediate portion thereof than at its ends.

Claim 38 (previously presented): The plasma reactor of Claim 23 wherein said conduit is formed of a metal material, said conduit having an insulating gap within a wall of the conduit extending transversely to said toroidal path and separating said conduit into two portions so as to prevent formation of a closed electrical path along the length of said conduit.

Claim 39 (previously presented): The plasma reactor of Claim 38 wherein said enclosure comprises a longitude side wall and an overlying lateral ceiling, and wherein said first and second openings extend through said ceiling.

Claim 40 (previously presented): The plasma reactor of Claim 38 wherein said enclosure comprises a longitudinal side wall and an overlying lateral ceiling, and wherein said first and second openings extend through said side wall.

Claim 41 (previously presented): The plasma reactor of Claim 38 wherein said overlying portion of said enclosure comprises a gas distribution plate, and wherein said height of said closed toroidal path along an axis perpendicular to a plane of said wafer support is the distance between said gas distribution plate and said wafer support.